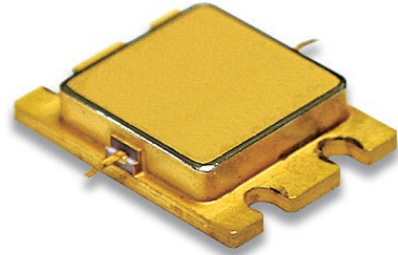


Features

- Frequency Band: 9-10GHz
- High Output Power: 49dBm
- High Power Gain: 8dB
- High PAE: 35%
- Standard Metal Package



Description

CWF0901 is an internally matched GaN FET by using planar thin-film matching technique. The FET provides up to 49 dBm output pulse/CW power for frequency band of 9-10GHz in a 50-ohm system.

Electrical Performance ($T_A=25^{\circ}\text{C}$, $V_{ds}=+28\text{V}$, $V_{gs}=-3\text{V}\sim-1.8\text{V}$, $I_{dq}=0.5\text{A}$)

Parameter	Min	Typ	Max	Unit
Frequency	9.0	-	10.0	GHz
Output Power	49.0	49.5	50.0	dBm
Power Gain	-	8.0	-	dB
Gain Flatness	-	-	2.0	dB
Power Added Efficiency	-	35%	-	-

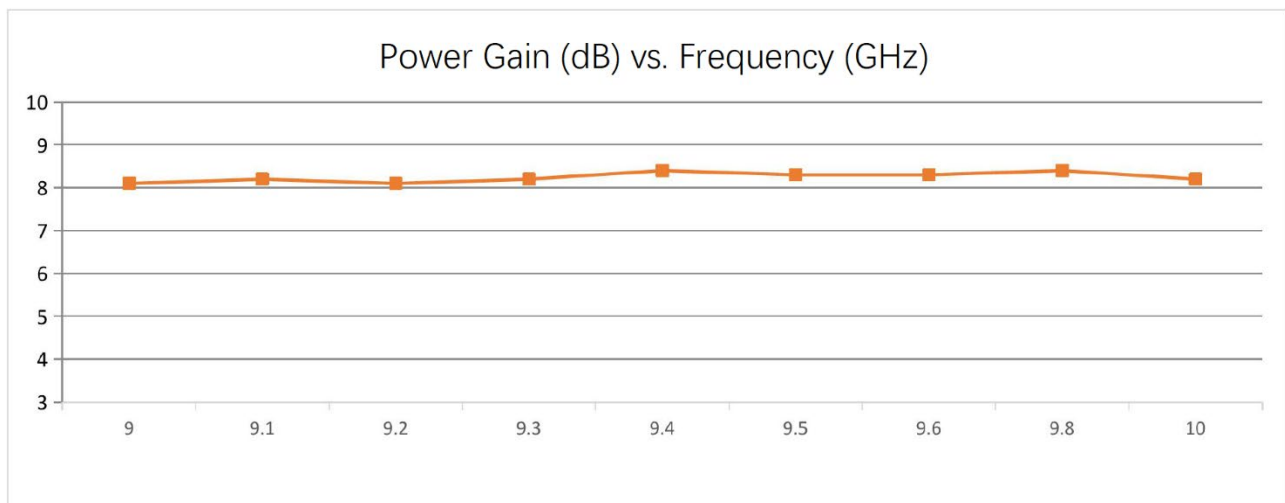


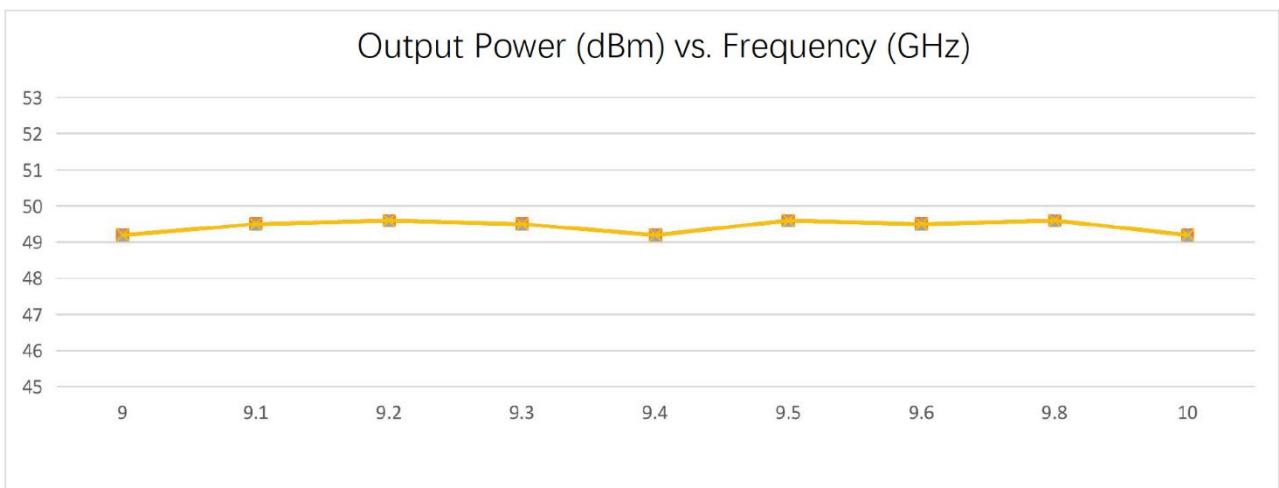
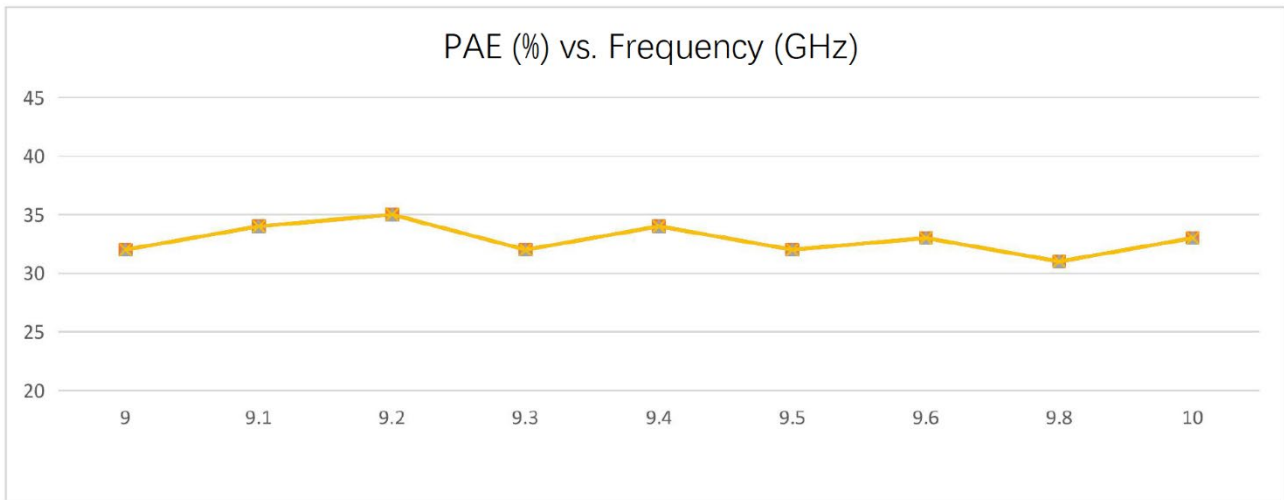
CWF0901

Internally Matched GaN FET, 9-10GHz

Pulse Width	-	-	CW	-
Duty Cycle	-	-	100%	-

Measured Performance ($T_A=25^\circ\text{C}$, $V_{ds}=+28\text{V}$, $V_{gs}=-3\text{V}\sim-1.8\text{V}$, $I_{dq}=0.5\text{A}$)



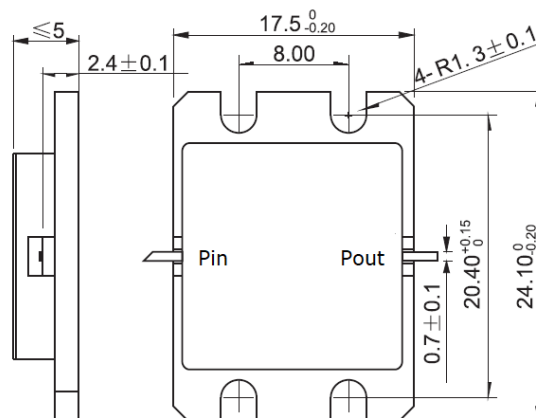


Absolute Maximum Ratings

Drain Voltage	+32V
Gate Voltage	-10V
Operating Temperature	-55°C to +125°C
Storage Temperature	-65°C to +150°C

Outline Drawing

Unit: mm



**ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS**